

Vishay Siliconix

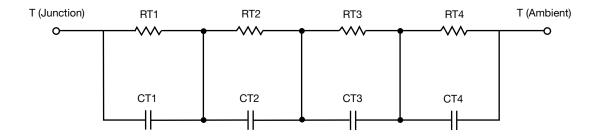
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	11.9104	35.6521m	N/A			
RT2	3.1921	157.7420m	N/A			
RT3	931.0189m	136.1924m	N/A			
RT4	23.9695	70.4392m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	8.2562	207.7579m	N/A			
CT2	1.0641	93.8616m	N/A			
CT3	147.3202m	7.5702m	N/A			
CT4	4.0108	956.4435m	N/A			

Note

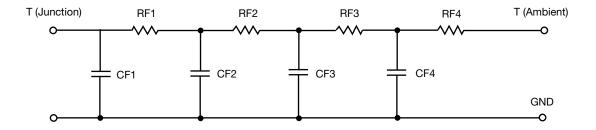
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	884.7234m	164.5848m	N/A			
RF2	6.5762	171.0568m	N/A			
RF3	23.1425	31.4611m	N/A			
RF4	9.4830	32.8974m	N/A			
	THERMAL CAPACI	TANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	24.3391m	6.6462m	N/A			
CF2	882.6174m	53.8870m	N/A			
CF3	1.7594	626.8623m	N/A			
CF4	2.6137	13.6994m	N/A			

Note

• n/a indicates not applicable





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